Giuseppe Iannaccone

List of Publications by Year
in descending order

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333 papers	10,853 citations	53660 45 h-index	38300 95 g-index
339 all docs	339 docs citations	339 times ranked	12376 citing authors

#	Article	IF	Citations
1	Electronics based on two-dimensional materials. Nature Nanotechnology, 2014, 9, 768-779.	15.6	2,505
2	Water-based and biocompatible 2D crystal inks for all-inkjet-printed heterostructures. Nature Nanotechnology, 2017, 12, 343-350.	15.6	440
3	Design criteria for the RF section of UHF and microwave passive RFID transponders. IEEE Transactions on Microwave Theory and Techniques, 2005, 53, 2978-2990.	2.9	340
4	Quantum engineering of transistors based on 2D materials heterostructures. Nature Nanotechnology, 2018, 13, 183-191.	15.6	319
5	Simulation of Graphene Nanoribbon Field-Effect Transistors. IEEE Electron Device Letters, 2007, 28, 760-762.	2.2	295
6	Performance of arsenene and antimonene double-gate MOSFETs from first principles. Nature Communications, 2016, 7, 12585.	5.8	278
7	A 2.6 nW, 0.45 V Temperature-Compensated Subthreshold CMOS Voltage Reference. IEEE Journal of Solid-State Circuits, 2011, 46, 465-474.	3.5	244
8	A Sub-1-V, 10 ppm/<formula formulatype="inline"> <tex>^{circ}</tex></formula>C, Nanopower Voltage Reference Generator. IEEE Journal of Solid-State Circuits, 2007, 42, 1536-1542.	3.5	240
9	Low-Power Wearable ECG Monitoring System for Multiple-Patient Remote Monitoring. IEEE Sensors Journal, 2016, 16, 5452-5462.	2.4	184
10	Threshold Voltage Instability in p-GaN Gate AlGaN/GaN HFETs. IEEE Transactions on Electron Devices, 2018, 65, 2454-2460.	1.6	156
11	Enhanced Shot Noise in Resonant Tunneling: Theory and Experiment. Physical Review Letters, 1998, 80, 1054-1057.	2.9	154
12	Performance Comparison of Graphene Nanoribbon FETs With Schottky Contacts and Doped Reservoirs. IEEE Transactions on Electron Devices, 2008, 55, 2314-2323.	1.6	138
13	Ultralow-Voltage Bilayer Graphene Tunnel FET. IEEE Electron Device Letters, 2009, 30, 1096-1098.	2.2	138
14	Multiscale Modeling for Graphene-Based Nanoscale Transistors. Proceedings of the IEEE, 2013, 101, 1653-1669.	16.4	138
15	Lateral Grapheneâ€“hBCN Heterostructures as a Platform for Fully Two-Dimensional Transistors. ACS Nano, 2012, 6, 2642-2648.	7.3	132
16	Last-Meter Smart Grid Embedded in an Internet-of-Things Platform. IEEE Transactions on Smart Grid, 2015, 6, 468-476.	6.2	131
17	Low-voltage 2D materials-based printed field-effect transistors for integrated digital and analog electronics on paper. Nature Communications, 2020, 11, 3566.	5.8	120
18	Electrical properties of graphene-metal contacts. Scientific Reports, 2017, 7, 5109.	1.6	119

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19	Gate-Tunable Atomically Thin Lateral MoS₂ Schottky Junction Patterned by Electron Beam. Nano Letters, 2016, 16, 3788-3794.	4.5	99
20	All-2D Material Inkjet-Printed Capacitors: Toward Fully Printed Integrated Circuits. ACS Nano, 2019, 13, 54-60.	7.3	95
21	An energy case for hybrid datacenters. Operating Systems Review (ACM), 2010, 44, 76-80.	1.5	92
22	A Three-Dimensional Simulation Study of the Performance of Carbon Nanotube Field-Effect Transistors With Doped Reservoirs and Realistic Geometry. IEEE Transactions on Electron Devices, 2006, 53, 1782-1788.	1.6	84
23	On the Possibility of Tunable-Gap Bilayer Graphene FET. IEEE Electron Device Letters, 2009, 30, 261-264.	2.2	84
24	Heterojunction Hybrid Devices from Vapor Phase Grown MoS2. Scientific Reports, 2014, 4, 5458.	1.6	80
25	Design of a 75â€nW, 0.5â€V subthreshold complementary metalâ€“oxideâ€“semiconductor operational amplifier. International Journal of Circuit Theory and Applications, 2014, 42, 967-977.	1.3	75
26	Analogue two-dimensional semiconductor electronics. Nature Electronics, 2020, 3, 486-491.	13.1	74
27	An Ultralow-Voltage Energy-Efficient Level Shifter. IEEE Transactions on Circuits and Systems II: Express Briefs, 2017, 64, 61-65.	2.2	67
28	Shot noise in resonant-tunneling structures. Physical Review B, 1997, 55, 4539-4550.	1.1	64
29	Velocity saturation in few-layer MoS2 transistor. Applied Physics Letters, 2013, 103, .	1.5	64
30	A Sub-<inline-formula> <tex-math notation="LaTeX">${oldsymbol kT}/oldsymbol q$ </tex-math></inline-formula> Voltage Reference Operating at 150 mV. IEEE Transactions on Very Large Scale Integration (VLSI) Systems, 2015, 23, 1547-1551.	2.1	64
31	Physics-Based Compact Model of Nanoscale MOSFETsâ€”Part I: Transition From Drift-Diffusion to Ballistic Transport. IEEE Transactions on Electron Devices, 2005, 52, 1795-1801.	1.6	61
32	A Semianalytical Model of Bilayer-Graphene Field-Effect Transistor. IEEE Transactions on Electron Devices, 2009, 56, 2979-2986.	1.6	59
33	CMOS Silicon Physical Unclonable Functions Based on Intrinsic Process Variability. IEEE Journal of Solid-State Circuits, 2011, 46, 1456-1463.	3.5	57
34	An Open-Source Multiscale Framework for the Simulation of Nanoscale Devices. IEEE Transactions on Electron Devices, 2014, 61, 48-53.	1.6	56
35	General relation between density of states and dwell times in mesoscopic systems. Physical Review B, 1995, 51, 4727-4729.	1.1	54
36	Effects due to backscattering and pseudogap features in graphene nanoribbons with single vacancies. Physical Review B, 2010, 81, .	1.1	54

#	Article	IF	Citations
37	Modeling and manufacturability assessment of bistable quantum-dot cells. Journal of Applied Physics, 1999, 85, 2962-2971.	1.1	52
38	Very Large Current Modulation in Vertical Heterostructure Graphene/hBN Transistors. IEEE Transactions on Electron Devices, 2013, 60, 268-273.	1.6	52
39	Three-Dimensional Simulation of One-Dimensional Transport in Silicon Nanowire Transistors. IEEE Nanotechnology Magazine, 2007, 6, 524-529.	1.1	51
40	Simulation of hydrogenated graphene field-effect transistors through a multiscale approach. Physical Review B, 2010, 82, .	1.1	50
41	Growthâ€Induced Strain in Chemical Vapor Deposited Monolayer MoS₂: Experimental and Theoretical Investigation. Advanced Materials Interfaces, 2017, 4, 1700031.	1.9	50
42	Three-dimensional simulation of nanocrystal Flash memories. Applied Physics Letters, 2001, 78, 2046-2048.	1.5	49
43	Strong mobility degradation in ideal graphene nanoribbons due to phonon scattering. Applied Physics Letters, 2011, 98, .	1.5	49
44	A SPICE-Compatible Model of MOS-Type Graphene Nano-Ribbon Field-Effect Transistors Enabling Gate- and Circuit-Level Delay and Power Analysis Under Process Variation. IEEE Nanotechnology Magazine, 2015, 14, 1068-1082.	1.1	49
45	GaN Nanowire n-MOSFET With 5 nm Channel Length for Applications in Digital Electronics. IEEE Electron Device Letters, 2017, 38, 859-862.	2.2	48
46	Physics-Based Compact Model of Nanoscale MOSFETsâ€"Part II: Effects of Degeneracy on Transport. IEEE Transactions on Electron Devices, 2005, 52, 1802-1806.	1.6	46
47	Electric Field Control of Spin Rotation in Bilayer Graphene. Nano Letters, 2010, 10, 4463-4469.	4.5	45
48	Lateral Heterostructure Field-Effect Transistors Based on Two-Dimensional Material Stacks with Varying Thickness and Energy Filtering Source. ACS Nano, 2020, 14, 1982-1989.	7.3	43
49	Ultralow Specific Contact Resistivity in Metalâ€"Graphene Junctions via Contact Engineering. Advanced Materials Interfaces, 2019, 6, 1801285.	1.9	41
50	Modeling of Tunnelling Currents in Hf-Based Gate Stacks as a Function of Temperature and Extraction of Material Parameters. IEEE Transactions on Electron Devices, 2007, 54, 83-89.	1.6	40
51	Two-dimensional hole precession in an all-semiconductor spin field effect transistor. Physical Review B, 2004, 69, .	1.1	39
52	Atomistic Investigation of Low-Field Mobility in Graphene Nanoribbons. IEEE Transactions on Electron Devices, 2011, 58, 2824-2830.	1.6	39
53	Bilayer Graphene Transistors for Analog Electronics. IEEE Transactions on Electron Devices, 2014, 61, 729-733.	1.6	38
54	Transistor Concepts Based on Lateral Heterostructures of Metallic and Semiconducting Phases of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>MoS</mml:mi></mml:mrow><mml:mrow><mml:mn>2</mml:mn></m Physical Review Applied, 2017, 8, .	1.5	38

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55	A SPICE-Compatible Model of Graphene Nano-Ribbon Field-Effect Transistors Enabling Circuit-Level Delay and Power Analysis under Process Variation. , 2013, , .		37
56	High performance metalâ€“insulatorâ€“graphene diodes for radio frequency power detection application. Nanoscale, 2017, 9, 11944-11950.	2.8	37
57	First-Principles Simulations of FETs Based on Two-Dimensional InSe. IEEE Electron Device Letters, 2018, 39, 626-629.	2.2	36
58	Coupled Mode Space Approach for the Simulation of Realistic Carbon Nanotube Field-Effect Transistors. IEEE Nanotechnology Magazine, 2007, 6, 475-480.	1.1	35
59	Analytical Model of One-Dimensional Carbon-Based Schottky-Barrier Transistors. IEEE Transactions on Electron Devices, 2010, 57, 1616-1625.	1.6	35
60	A QCA cell in silicon-on-insulator technology: theory and experiment. Superlattices and Microstructures, 2003, 34, 205-211.	1.4	34
61	Effective Bohm Quantum Potential for device simulators based on drift-diffusion and energy transport. , 2004, , 275-278.		34
62	Modelling and simulation challenges for nanoscale MOSFETs in the ballistic limit. Solid-State Electronics, 2004, 48, 581-587.	0.8	33
63	Low-Voltage Low-Power CMOS Oscillator with Low Temperature and Process Sensitivity. , 2007, , .		33
64	Two-Dimensional Tunnel Transistors Based on ${m Bi}_{2}{m Se}_{3}$ Thin Film. IEEE Electron Device Letters, 2014, 35, 129-131.	2.2	32
65	Modeling of Electron Devices Based on 2-D Materials. IEEE Transactions on Electron Devices, 2018, 65, 4167-4179.	1.6	32
66	Junction Engineering of 1T-DRAMs. IEEE Electron Device Letters, 2013, 34, 408-410.	2.2	31
67	Reconfigurable Diodes Based on Vertical WSe₂ Transistors with van der Waals Bonded Contacts. Advanced Materials, 2018, 30, e1707200.	11.1	31
68	Power Electronics Based on Wide-Bandgap Semiconductors: Opportunities and Challenges. IEEE Access, 2021, 9, 139446-139456.	2.6	31
69	Graphene-based lateral heterostructure transistors exhibit better intrinsic performance than graphene-based vertical transistors as post-CMOS devices. Scientific Reports, 2015, 4, 6607.	1.6	29
70	Simulation of a quantum-dot flash memory. Journal of Applied Physics, 1998, 84, 5032-5036.	1.1	28
71	Rashba spin precession in quantum-Hall edge channels. Physical Review B, 2005, 71, .	1.1	28
72	An ultra-low-power, temperature compensated voltage reference generator. , 0, , .		28

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73	Model of tunneling transistors based on graphene on SiC. Applied Physics Letters, 2010, 96, 133508.	1.5	28
74	Comparison of Modeling Approaches for the Capacitanceâ€“Voltage and Currentâ€“Voltage Characteristics of Advanced Gate Stacks. IEEE Transactions on Electron Devices, 2007, 54, 106-114.	1.6	27
75	Perspectives of graphene nanoelectronics: probing technological options with modeling. , 2009, , .		27
76	Vertical transport in graphene-hexagonal boron nitride heterostructure devices. Scientific Reports, 2015, 5, 14519.	1.6	27
77	Semiclassical simulation of quantum cellular automaton circuits. International Journal of Circuit Theory and Applications, 2001, 29, 37-47.	1.3	26
78	On the role of interface states in low-voltage leakage currents of metalâ€“oxideâ€“semiconductor structures. Applied Physics Letters, 2002, 80, 4597-4599.	1.5	26
79	Theory and experiment of suppressed shot noise in stress-induced leakage currents. IEEE Transactions on Electron Devices, 2003, 50, 1363-1369.	1.6	26
80	CMOS unclonable system for secure authentication based on device variability. , 2008, , .		26
81	Flexible One-Dimensional Metalâ€“Insulatorâ€“Graphene Diode. ACS Applied Electronic Materials, 2019, 1, 945-950.	2.0	26
82	Analytical model for the 1âˆ•f noise in the tunneling current through metal-oxide-semiconductor structures. Journal of Applied Physics, 2009, 106, .	1.1	25
83	Analysis of shot noise suppression in mesoscopic cavities in a magnetic field. Europhysics Letters, 2006, 73, 574-580.	0.7	24
84	A 109 nW, 44 ppm/Â°C CMOS Current Reference with Low Sensitivity to Process Variations. , 2007, , .		24
85	First principles investigation of tunnel FETs based on nanoribbons from topological two-dimensional materials. Nanoscale, 2017, 9, 19390-19397.	2.8	24
86	A Steep-Slope MoS₂-Nanoribbon MOSFET Based on an Intrinsic Cold-Contact Effect. IEEE Electron Device Letters, 2019, 40, 1550-1553.	2.2	24
87	Thermal behavior of quantum cellular automaton wires. Journal of Applied Physics, 2000, 87, 7320-7325.	1.1	23
88	Enhancement and suppression of shot noise in capacitively coupled metallic double dots. Physical Review B, 2002, 65, .	1.1	23
89	Shot Noise Suppression in Quasi-One-Dimensional Field-Effect Transistors. IEEE Transactions on Electron Devices, 2009, 56, 2137-2143.	1.6	23
90	Model and Performance Evaluation of Field-Effect Transistors Based on Epitaxial Graphene on SiC. IEEE Transactions on Electron Devices, 2010, 57, 1936-1941.	1.6	23

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91	Compact formula for the density of states in a quantum well. Physical Review B, 1996, 53, 2020-2025.	1.1	22
92	Statistical model of dephasing in mesoscopic devices introduced in the scattering matrix formalism. Physical Review B, 2004, 69, .	1.1	22
93	A 300 nW, 12 ppm/Â°C Voltage Reference in a Digital 0.35 Î¼m CMOS Process. , 0, , .		22
94	The Role of Silicon Substrate on the Leakage Current Through GaN-on-Si Epitaxial Layers. IEEE Transactions on Electron Devices, 2018, 65, 51-58.	1.6	22
95	Suppressed shot noise in trap-assisted tunneling of metalâ€“oxideâ€“semiconductor capacitors. Applied Physics Letters, 2000, 77, 2876-2878.	1.5	21
96	Effect of Dephasing on the Current Statistics of Mesoscopic Devices. Physical Review Letters, 2004, 93, 256803.	2.9	21
97	Analytical and Numerical Investigation of Noise in Nanoscale Ballistic Field Effect Transistors. Journal of Computational Electronics, 2004, 3, 199-202.	1.3	21
98	Ultra Low Power RF Section of a Passive Microwave RFID Transponder in 0.35 Î¼m BiCMOS. , 0, , .		21
99	Quantum analysis of shot noise suppression in a series of tunnel barriers. Physical Review B, 2009, 79, .	1.1	21
100	A picopower temperatureâ€compensated, subthreshold CMOS voltage reference. International Journal of Circuit Theory and Applications, 2014, 42, 1306-1318.	1.3	21
101	Modeling of ballistic nanoscale metal-oxide-semiconductor field effect transistors. Applied Physics Letters, 2002, 81, 3672-3674.	1.5	20
102	Four-phase power clock generator for adiabatic logic circuits. Electronics Letters, 2002, 38, 689.	0.5	20
103	Analytical Model of the Effects of a Nonuniform Distribution of Stored Charge on the Electrical Characteristics of Discrete-Trap Nonvolatile Memories. IEEE Nanotechnology Magazine, 2005, 4, 360-368.	1.1	20
104	Direct Solution of the Boltzmann Transport Equation and Poissonâ€“SchrÃ–dinger Equation for Nanoscale MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 2901-2909.	1.6	20
105	Highâ€Performance 2D pâ€Type Transistors Based on GaSe Layers: An Ab Initio Study. Advanced Electronic Materials, 2017, 3, 1600399.	2.6	20
106	Analog Vector-Matrix Multiplier Based on Programmable Current Mirrors for Neural Network Integrated Circuits. IEEE Access, 2020, 8, 203525-203537.	2.6	20
107	Low-Power Artificial Neural Network Perceptron Based on Monolayer MoS₂. ACS Nano, 2022, 16, 3684-3694.	7.3	20
108	Characteristic times in the motion of a particle. Physical Review B, 1994, 49, 16548-16560.	1.1	19

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109	Status and perspectives of nanoscale device modelling. Nanotechnology, 2001, 12, 136-142.	1.3	18
110	Performance assessment of adiabatic quantum cellular automata. Journal of Applied Physics, 2001, 89, 6435-6443.	1.1	18
111	Simulation of time evolution of clocked and nonclocked quantum cellular automaton circuits. Journal of Applied Physics, 2002, 92, 3169-3178.	1.1	18
112	Hadron collider triggers with high-quality tracking at very high event rates. IEEE Transactions on Nuclear Science, 2004, 51, 391-400.	1.2	18
113	Modelling and simulation of charging and discharging processes in nanocrystal flash memories during program and erase operations. Solid-State Electronics, 2005, 49, 1745-1753.	0.8	18
114	A comparison of advanced transport models for the computation of the drain current in nanoscale nMOSFETs. Solid-State Electronics, 2009, 53, 1293-1302.	0.8	18
115	Operation of quantum cellular automaton cells with more than two electrons. Applied Physics Letters, 1999, 75, 3198-3200.	1.5	17
116	The fast tracker processor for hadron collider triggers. IEEE Transactions on Nuclear Science, 2001, 48, 575-580.	1.2	17
117	Detailed Modeling of Sub-100-nm MOSFETs Based on SchrÃ–dinger DD Per Subband and Experiments and Evaluation of the Performance Gap to Ballistic Transport. IEEE Transactions on Electron Devices, 2005, 52, 1851-1858.	1.6	17
118	Geometrical Effects on Valley-Orbital Filling Patterns in Silicon Quantum Dots for Robust Qubit Implementation. Applied Physics Express, 2012, 5, 124001.	1.1	17
119	Comparison of short-channel effects in monolayer MoS2 based junctionless and inversion-mode field-effect transistors. Applied Physics Letters, 2016, 108, 023506.	1.5	17
120	Tunnel-Field-Effect Spin Filter from Two-Dimensional Antiferromagnetic Stanene. Physical Review Applied, 2018, 10, .	1.5	17
121	Unified approach to electron transport in double-barrier structures. Physical Review B, 1995, 52, 17406-17412.	1.1	16
122	The effect of quantum confinement and discrete dopants in nanoscale 50 nm n-MOSFETs: a three-dimensional simulation. Nanotechnology, 2002, 13, 294-298.	1.3	16
123	Barrier Lowering and Backscattering Extraction in Short-Channel MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 2132-2137.	1.6	16
124	Material-Device-Circuit Co-optimization of 2D Material based FETs for Ultra-Scaled Technology Nodes. Scientific Reports, 2017, 7, 5016.	1.6	16
125	A portable class of 3â€transistor current references with lowâ€power subâ€0.5Â<scp>V</scp> operation. International Journal of Circuit Theory and Applications, 2018, 46, 779-795.	1.3	16
126	Inkjet-printed low-dimensional materials-based complementary electronic circuits on paper. Npj 2D Materials and Applications, 2021, 5, .	3.9	16

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127	Noise measurements in resonant tunnelling structures as a function of current and temperature. Electronics Letters, 1995, 31, 503-505.	0.5	15
128	Modelling of self-organized InAs quantum dots embedded in an AlGaAs/GaAs heterostructure. Nanotechnology, 2002, 13, 263-266.	1.3	15
129	Ultra-low-power temperature compensated voltage reference generator. Microelectronics Journal, 2006, 37, 1072-1079.	1.1	15
130	Insights on radio frequency bilayer graphene FETs. , 2012, , .		15
131	Simulation of the Performance of Graphene FETs With a Semiclassical Model, Including Band-to-Band Tunneling. IEEE Transactions on Electron Devices, 2014, 61, 1567-1574.	1.6	15
132	Performance Analysis of Graphene Bilayer Transistors Through Tight-Binding Simulations. , 2009, , .		14
133	Inkjet-printed graphene Hall mobility measurements and low-frequency noise characterization. Nanoscale, 2020, 12, 6708-6716.	2.8	14
134	Proposed experiment to assess operation of quantum cellular automaton cells. Journal of Applied Physics, 2001, 90, 6428-6433.	1.1	13
135	Code for the 3D Simulation of Nanoscale Semiconductor Devices, Including Drift-Diffusion and Ballistic Transport in 1D and 2D Subbands, and 3D Tunneling. Journal of Computational Electronics, 2005, 4, 63-66.	1.3	13
136	Advantages of the FinFET architecture in SONOS and Nanocrystal memory devices. , 2007, , .		13
137	A model for MOS gate stack quality evaluation based on the gate current 1/f noise. , 2008, , .		13
138	Statistical theory of shot noise in quasi-one-dimensional field-effect transistors in the presence of electron-electron interaction. Physical Review B, 2010, 81, .	1.1	13
139	Drift velocity peak and negative differential mobility in high field transport in graphene nanoribbons explained by numerical simulations. Applied Physics Letters, 2011, 99, .	1.5	13
140	On Transport in Vertical Graphene Heterostructures. IEEE Electron Device Letters, 2014, 35, 966-968.	2.2	13
141	Cold-source paradigm for steep-slope transistors based on van der Waals heterojunctions. Physical Review Research, 2020, 2, .	1.3	13
142	Characterization of soft breakdown in thin oxide NMOSFETs based on the analysis of the substrate current. IEEE Transactions on Electron Devices, 2001, 48, 1109-1113.	1.6	12
143	Performance of carbon nanotube field effect transistors with doped source and drain extensions and arbitrary geometry. , 0, , .		12
144	Three-Dimensional Simulation of Realistic Single Electron Transistors. IEEE Nanotechnology Magazine, 2005, 4, 415-421.	1.1	12

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145	A Sub-1 V, 10 ppm/Â°C, Nanopower Voltage Reference Generator. , 2006, , .		12
146	A three-dimensional solver of the SchrÃ¶dinger equation in momentum space for the detailed simulation of nanostructures. Nanotechnology, 2002, 13, 369-372.	1.3	11
147	NANOTCAD2D: Two-dimensional code for the simulation of nanoelectronic devices and structures. Computational Materials Science, 2003, 28, 342-352.	1.4	11
148	Numerical investigation of shot-noise suppression in diffusive conductors. Physical Review B, 2003, 67, .	1.1	11
149	Dependence of the programming window of silicon-on-insulator nanocrystal memories on channel width. Applied Physics Letters, 2005, 86, 113502.	1.5	11
150	Ultra-low-power series voltage regulator for passive RFID transponders with subthreshold logic. Electronics Letters, 2006, 42, 1350.	0.5	11
151	Shot noise partial suppression in the SILO regime. Microelectronics Reliability, 2000, 40, 1605-1608.	0.9	10
152	Quantum confinement in silicon-germanium electron waveguides. Nanotechnology, 2002, 13, 267-273.	1.3	10
153	Extraction of parameters of surface states from experimental test structures. Nanotechnology, 2002, 13, 373-377.	1.3	10
154	Channel noise modelling of nanoMOSFETs in a partially ballistic transport regime. Journal of Computational Electronics, 2006, 5, 91-95.	1.3	10
155	Can graphene outperform indium tin oxide as transparent electrode in organic solar cells?. 2D Materials, 2015, 2, 045006.	2.0	10
156	Internet-of-things infrastructure as a platform for distributed measurement applications. , 2015, , .		10
157	Insights on the physics and application of off-plane quantum transport through graphene and 2D materials. Solid-State Electronics, 2016, 115, 213-218.	0.8	10
158	A 220-mV input, 8.6 step-up voltage conversion ratio, 10.45-Î¼W output power, fully integrated switched-capacitor converter for energy harvesting. , 2017, , .		10
159	Stacking and interlayer electron transport in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>MoS</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math> Physical Review B, 2018, 98, .	1.1	10
160	On the approach to the stationary-state-scattering limit within Bohmian mechanics. Physics Letters, Section A: General, Atomic and Solid State Physics, 1995, 208, 17-24.	0.9	9
161	Probing Pauli blocking with shot noise in resonant tunneling diodes: Experiment and theory. Physical Review B, 2007, 75, .	1.1	9
162	Atomistic quantum transport modeling of metal-graphene nanoribbon heterojunctions. Physical Review B, 2010, 82, .	1.1	9

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163	A Microscopically Accurate Model of Partially Ballistic NanoMOSFETs in Saturation Based on Channel Backscattering. IEEE Transactions on Electron Devices, 2011, 58, 691-697.	1.6	9
164	Compact drain-current model for reproducing advanced transport models in nanoscale double-gate MOSFETs. Semiconductor Science and Technology, 2011, 26, 095015.	1.0	9
165	Quantum transport modeling of defected graphene nanoribbons. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 981-984.	1.3	9
166	Characterization and modeling of CMOS-compatible acoustical particle velocity sensors for applications requiring low supply voltages. Sensors and Actuators A: Physical, 2015, 229, 192-202.	2.0	9
167	Transport properties in partially overlapping van der Waals junctions through a multiscale investigation. Physical Review B, 2021, 104, .	1.1	9
168	Adiabatic 4-bit adders: comparison of performance and robustness against technology parameter variations. , 0, , .		8
169	Three-Dimensional Simulation of the Dependence of the Programming Window of SOI Nanocrystal Memories on the Channel Width. IEEE Nanotechnology Magazine, 2005, 4, 326-330.	1.1	8
170	Engineering Interband Tunneling in Nanowires With Diamond Cubic or Zincblende Crystalline Structure Based on Atomistic Modeling. IEEE Nanotechnology Magazine, 2013, 12, 839-842.	1.1	8
171	Low frequency current noise in unstressed/stressed thin oxide metal-oxide-semiconductor capacitors. Solid-State Electronics, 2002, 46, 1807-1813.	0.8	7
172	Ultra-low-power series voltage regulator for passive microwave RFID transponders. , 2005, , .		7
173	Equivalent resistance and noise of cascaded mesoscopic cavities. International Journal of Circuit Theory and Applications, 2007, 35, 295-304.	1.3	7
174	Analytical Model of Nanowire FETs in a Partially Ballistic or Dissipative Transport Regime. IEEE Transactions on Electron Devices, 2009, , .	1.6	7
175	Physical insights on graphene nanoribbon mobility through atomistic simulations. , 2009, , .		7
176	Multi-scale simulation of partially unzipped CNT hetero-junction Tunneling Field Effect Transistor. , 2010, , .		7
177	An Approach Based on Sensitivity Analysis for the Evaluation of Process Variability in Nanoscale MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 2266-2273.	1.6	7
178	Modeling of nanoscale devices with carriers obeying a three-dimensional density of states. Journal of Applied Physics, 2013, 113, 143711.	1.1	7
179	Charge Injection in Normally-Off p-GaN Gate AlGaN/GaN-on-Si HFETs. , 2018, , .		7
180	Electronic Transport in 2Dâ€Based Printed FETs from a Multiscale Perspective. Advanced Electronic Materials, 2022, 8, 2100972.	2.6	7

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181	Coulomb breach effect emerging in shot noise. Nanotechnology, 1999, 10, 97-101.	1.3	6
182	Evaluation of the effect of fabrication tolerances on the ground-state energy of electrostatically defined quantum dots. Superlattices and Microstructures, 2000, 27, 359-362.	1.4	6
183	A pipeline of associative memory boards for track finding. IEEE Transactions on Nuclear Science, 2001, 48, 595-600.	1.2	6
184	Perspectives and challenges in nanoscale device modeling. Microelectronics Journal, 2005, 36, 614-618.	1.1	6
185	Experimental and theoretical analysis of scaling issues in dual-bit discrete trap non-volatile memories. , 2005, , .		6
186	Analytical model for nanowire and nanotube transistors covering both dissipative and ballistic transport. , 0, , .		6
187	Threshold voltage dispersion and impurity scattering limited mobility in carbon nanotube field effect transistors with randomly doped reservoirs. Solid-State Device Research Conference, 2008 ESSDERC 2008 38th European, 2006, , .	0.0	6
188	Performance Comparison of Graphene Nanoribbon Schottky Barrier and MOS FETs. , 2007, , .		6
189	Shot noise in quasi one-dimensional FETs. , 2008, , .		6
190	Study of Warm-Electron Injection in Double-Gate SONOS by Full-Band Monte Carlo Simulation. IEEE Electron Device Letters, 2008, 29, 1242-1244.	2.2	6
191	Nanodevices in Flatland: Two-dimensional graphene-based transistors with high I<inf>on</inf>/I<inf>off</inf> ratio. , 2011, , .		6
192	Design of a nanopower current reference with reduced process variability. Analog Integrated Circuits and Signal Processing, 2013, 77, 45-53.	0.9	6
193	Implementation of nanoscale double-gate CMOS circuits using compact advanced transport models. Microelectronics Journal, 2013, 44, 80-85.	1.1	6
194	Sensitivity-based investigation of threshold voltage variability in 32-nm flash memory cells and MOSFETs. Solid-State Electronics, 2013, 84, 127-131.	0.8	6
195	A critical review of reduced one-dimensional beam models of piezoelectric composite beams. Journal of Intelligent Material Systems and Structures, 2019, 30, 1148-1162.	1.4	6
196	Vertical Heterostructures between Transitionâ€Metal Dichalcogenidesâ€”A Theoretical Analysis of the NbS2/WSe2 Junction. Advanced Electronic Materials, 2022, 8, .	2.6	6
197	Time Domain Analog Neuromorphic Engine Based on High-Density Non-Volatile Memory in Single-Poly CMOS. IEEE Access, 2022, 10, 49154-49166.	2.6	6
198	Theory of conductance and noise additivity in parallel mesoscopic conductors. Physical Review B, 1997, 56, 12104-12107.	1.1	5

#	Article	IF	Citations
199	Simulation of a non-invasive charge detector for quantum cellular automata. Thin Solid Films, 1998, 336, 145-148.	0.8	5
200	Tuning of surface boundary conditions for the 3D simulation of gated heterostructures. Superlattices and Microstructures, 2000, 27, 369-372.	1.4	5
201	Monte Carlo simulation of electromigration in polycrystalline metal stripes. Semiconductor Science and Technology, 2000, 15, 608-612.	1.0	5
202	Current noise at the oxide hard-breakdown. Microelectronic Engineering, 2001, 59, 43-47.	1.1	5
203	Experimental and theoretical investigation of quantum point contacts for the validation of models for surface states. Nanotechnology, 2002, 13, 299-303.	1.3	5
204	Three-dimensional atomistic simulation of carbon nanotube FETs with realistic geometry. , 0, , .		5
205	Ultra-low power PSK backscatter modulator for UHF and microwave RFID transponders. Microelectronics Journal, 2006, 37, 627-629.	1.1	5
206	A Voltage Regulator for Subthreshold Logic with Low Sensitivity to Temperature and Process Variations. , 2007, , .		5
207	Corrections to â€œa three-dimensional simulation study of the performance of carbon nanotube field-effect transistors with doped reservoirs and realistic geometryâ€•[Aug 06 1782-1788]. IEEE Transactions on Electron Devices, 2008, 55, 1094-1095.	1.6	5
208	Enhanced shot noise in carbon nanotube field-effect transistors. Applied Physics Letters, 2009, 95, 252108.	1.5	5
209	Semi-analytical model for schottky-barrier carbon nanotube and graphene nanoribbon transistors. , 2010, , .		5
210	A Backscattering Model Incorporating the Effective Carrier Temperature in Nano-MOSFET. IEEE Electron Device Letters, 2011, 32, 853-855.	2.2	5
211	An intragrid implementation embedded in an Internet of Things platform. , 2013, , .		5
212	A subâ€1â€‰V nanopower temperatureâ€compensated subâ€threshold CMOS voltage reference with 0.065%/V line sensitivity. International Journal of Circuit Theory and Applications, 2015, 43, 421-426.	1.3	5
213	Suppressed and enhanced shot noise in one dimensional field-effect transistors. Journal of Computational Electronics, 2015, 14, 94-106.	1.3	5
214	Temperature Compensation of Silicon LamÃ© Resonators Using Etch Holes: Theory and Design Methodology. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2017, 64, 879-887.	1.7	5
215	Physical insights into the operation of a 1-nm gate length transistor based on MoS2 with metallic carbon nanotube gate. Applied Physics Letters, 2018, 113, .	1.5	5
216	Variabilityâ€aware design of a bandgap voltage reference with 0.18% standard deviation and 68ÂnW power consumption. International Journal of Circuit Theory and Applications, 2018, 46, 1985-1999.	1.3	5

#	Article	IF	Citations
217	Phonon-assisted carrier transport through a lattice-mismatched interface. NPG Asia Materials, 2019, 11, .	3.8	5
218	Physical insights on transistors based on lateral heterostructures of monolayer and multilayer PtSe2 via Ab initio modelling of interfaces. Scientific Reports, 2021, 11, 18482.	1.6	5
219	Resonant 90 degree shifter generator for 4-phase trapezoidal adiabatic logic. Advances in Radio Science, 0, 1, 243-246.	0.7	5
220	Program, Erase and Retention Times of Thin-oxide Flash-EEPROMs. VLSI Design, 2001, 13, 431-434.	0.5	4
221	Analysis of shot-noise suppression in disordered quantum wires. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 19, 107-111.	1.3	4
222	Hierarchical simulation of transport in silicon nanowire transistors. Journal of Computational Electronics, 2008, 7, 415-418.	1.3	4
223	Low-voltage nanopower clock generator for RFID applications. Microelectronics Journal, 2008, 39, 1736-1739.	1.1	4
224	Analytical drain current model reproducing advanced transport models in nanoscale cylindrical surrounding-gate (SRG) MOSFETs. Journal of Applied Physics, 2011, 110, 034510.	1.1	4
225	The challenging promise of 2D materials for electronics. , 2015, , .		4
226	A Simple Method for the Design of 1-D MEMS Flexural Phononic Crystals. IEEE Transactions on Electron Devices, 2016, 63, 4131-4137.	1.6	4
227	On current transients in MoS2 Field Effect Transistors. Scientific Reports, 2017, 7, 11575.	1.6	4
228	Theoretical Analysis of a 2D Metallic/Semiconducting Transitionâ€Metal Dichalcogenide NbS₂//WSe₂ Hybrid Interface. Advanced Theory and Simulations, 2020, 3, 2000164.	1.3	4
229	1/f Noise Characterization of Bilayer MoS₂ Fieldâ€Effect Transistors on Paper with Inkjetâ€Printed Contacts and hBN Dielectrics. Advanced Electronic Materials, 2021, 7, 2100283.	2.6	4
230	A 0.6Vâ€“1.8V Compact Temperature Sensor With 0.24 Â°C Resolution, Â±1.4 Â°C Inaccuracy and 1.06nJ per Conversion. IEEE Sensors Journal, 2022, 22, 11480-11488.	2.4	4
231	Assessment of paper-based MoS2 FET for Physically Unclonable Functions. Solid-State Electronics, 2022, 194, 108391.	0.8	4
232	Approaches to the tunneling time based on the Larmor clock and absorption probabilities as particular cases of the stay-time method. Physical Review B, 1994, 50, 14659-14662.	1.1	3
233	The fast tracker processor for hadronic collider triggers. , 0, , .		3
234	â€œAtomisticâ€ Quantum and Ballistic Effects in Nanoscale MOSFETs. Journal of Computational Electronics, 2003, 2, 123-126.	1.3	3

#	Article	IF	Citations
235	Physical Model for NAND operation in SOI and Body-Tied Nanocrystal FinFLASH memories. , 2007, , .		3
236	Low voltage hot-carrier programming of ultra-scaled SOI finflash memories. , 2007, , .		3
237	Numerical Analysis of Transport Properties of Boron-Doped Graphene FETs. , 2009, , .		3
238	Full band assessment of phonon-limited mobility in Graphene NanoRibbons. , 2010, , .		3
239	Noise in graphene and carbon nanotube devices. , 2011, , .		3
240	Variability-aware design of 55 nA current reference with 1.4% standard deviation and 290 nW power consumption. , 2012, , .		3
241	Understanding the nature of metal-graphene contacts: A theoretical and experimental study. , 2015, , .		3
242	Low energy/delay overhead level shifter for wideâ€range voltage conversion. International Journal of Circuit Theory and Applications, 2017, 45, 1637-1646.	1.3	3
243	Ballistic two-dimensional lateral heterojunction bipolar transistor. Physical Review Research, 2021, 3, .	1.3	3
244	Assessment of 2D-FET Based Digital and Analog Circuits on Paper. Solid-State Electronics, 2021, 185, 108063.	0.8	3
245	Three-Dimensional Simulations of Quantum Confinement and Random Dopants Effects in Nanoscale nMOSFETs. Journal of Computational and Theoretical Nanoscience, 2008, 5, 1115-1119.	0.4	3
246	Origin of the substrate current after soft-breakdown in thin oxide n-MOSFETs. , 1999, , .		2
247	A pipeline of associative memory boards for track finding. , 0, , .		2
248	Three-dimensional Statistical Modeling of the Effects of the Random Distribution of Dopants in Deep Sub-micron nMOSFETs. VLSI Design, 2001, 13, 425-429.	0.5	2
249	Modelling of trap assisted tunnelling through thin dielectric layers. Materials Science and Technology, 2002, 18, 736-738.	0.8	2
250	Ballistic Transport in SiGe and Strained-Si MOSFETs. Journal of Computational Electronics, 2003, 2, 309-312.	1.3	2
251	On the occurrence of few-electrons phenomena in ultra-scaled silicon nano-crystals memories. , 0, , .		2
252	Hierarchical tools for the simulation of nanoscale circuits and devices: from artificial to real molecules. IET Circuits, Devices and Systems, 2004, 151, 473.	0.6	2

#	Article	IF	Citations
253	Extraction of the trap distribution responsible for SILCs in MOS structures from the measurements and simulations of DC and noise properties. Microelectronics Reliability, 2004, 44, 1497-1501.	0.9	2
254	Universal signature of ballistic transport in nanoscale field effect transistors. , 0, , .		2
255	Numerical simulation of ballistic magnetoconductance and magnetic focusing in strained Siâ€“SiGe cavities. Nanotechnology, 2005, 16, S206-S210.	1.3	2
256	Time-Independent Simulation of QCA Circuits. , 2006, , 65-85.		2
257	Ultra-Low-Power Flash Memory in Standard 0.35 Î¼m CMOS for Passive Microwave RFID Transponders. , 0, , .		2
258	Noise and reliability in simulated thin metal films. Microelectronics Reliability, 2008, 48, 1015-1020.	0.9	2
259	Modeling the gate current 1/f noise and its application to advanced CMOS devices. , 2008, , .		2
260	A software platform for nanoscale device simulation and visualization. , 2009, , .		2
261	Analytical and TCAD-supported approach to evaluate intrinsic process variability in nanoscale MOSFETs. , 2009, , .		2
262	Physical insights on nanoscale FETs based on epitaxial graphene on SiC. , 2009, , .		2
263	Evaluation of threshold voltage dispersion in 45 nm CMOS technology with TCAD-based sensitivity analysis. , 2010, , .		2
264	Enhanced shot noise in carbon nanotube FETs due to electron-hole interaction. , 2010, , .		2
265	Relevance of the physics of off-plane transport through 2D materials on the design of vertical transistors. , 2015, , .		2
266	Two-dimensional transistors based on MoS<inf>2</inf> lateral heterostructures. , 2016, , .		2
267	Sub-Maxwellian Source Injection and Negative Differential Transconductance in Decorated Graphene Nanoribbons. Physical Review Applied, 2020, 14, .	1.5	2
268	Proposal of a physics-based compact model for nanoscale MOSFETs including the transition from drift-diffusion to ballistic transport. , 2004, , 363-366.		2
269	Detailed calculation of vertical electric field in thin oxide MOSFETs. Electronics Letters, 1999, 35, 1881.	0.5	1
270	Simulation of electromigration noise in polycrystalline metal stripes. Microelectronics Reliability, 2000, 40, 1955-1958.	0.9	1

#	Article	IF	Citations
271	Signatures of electron-electron interaction in nanoelectronic device shot noise. AIP Conference Proceedings, 2000, , .	0.3	1
272	Towards nanotechnology computer aided design: the NANOTCAD project. , 0, , .		1
273	NOISE AS A PROBE OF THE CHARGE TRANSPORT MECHANISMS THROUGH THIN OXIDES IN MOS STRUCTURES. Fluctuation and Noise Letters, 2001, 01, L61-L64.	1.0	1
274	Evaluation of performance and perspectives of nanocrystal flash memories based on 3D quantum modeling. , 0, , .		1
275	Electronic properties of functional nanocrystal layers for non-volatile memory applications. Materials Science and Technology, 2002, 18, 733-735.	0.8	1
276	Ballistic transport in nanoscale field effect transistors revealed by four-terminal DC characterization. Superlattices and Microstructures, 2003, 34, 271-275.	1.4	1
277	Two-dimensional modeling of etched strained-silicon quantum wires. Journal of Applied Physics, 2004, 95, 1251-1257.	1.1	1
278	Electrostatic effect of localised charge in dual bit memory cells with discrete traps. , 0, , .		1
279	Three-dimensional simulation of single electron transistors. , 0, , .		1
280	Subthreshold behavior of dual-bit nonvolatile memories with very small regions of trapped charge. IEEE Nanotechnology Magazine, 2006, 5, 373-378.	1.1	1
281	3D simulation of a silicon quantum dot in a magnetic field based on current spin density functional theory. Journal of Computational Electronics, 2007, 6, 191-194.	1.3	1
282	Effect of localization on the Fano factor of cascaded tunnel barriers. , 2009, , .		1
283	Comparison of advanced transport models for nanoscale nMOSFETs. , 2009, , .		1
284	Analytical drain current model reproducing advanced transport models in nanoscale double-gate (DG) MOSFETs. , 2011, , .		1
285	Two Dimensional Graphene/h-BCN Based Devices with Large Ion/Ioff Ratio for Digital Applications. Advances in Science and Technology, 0, , .	0.2	1
286	Optimization and benchmarking of graphene-based heterostructure FETs. , 2014, , .		1
287	MoS₂/graphene Lateral Heterostructure Field Effect Transistors. , 2021, , .		1
288	Semiclassical simulation of quantum cellular automaton circuits. International Journal of Circuit Theory and Applications, 2001, 29, 37-47.	1.3	1

#	Article	IF	Citations
289	Assessment of Two-Dimensional Materials-Based Technology for Analog Neural Networks. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2021, 7, 141-149.	1.1	1
290	Modeling of Shot Noise in Resonant Tunneling Structures. VLSI Design, 1998, 8, 449-453.	0.5	0
291	Detection of Quantum Cellular Automaton Action in Silicon-on-insulator Cells. VLSI Design, 2001, 13, 419-424.	0.5	0
292	Effects of quantum confinement and discrete dopants in nanoscale bulk-Si nMOSFET. , 0, , .		0
293	Techniques and methods for the simulation of nanoscale ballistic MOSFETs. , 0, , .		0
294	Evaluation of program, erase and retention times of flash memories with very thin gate dielectric. , 0, , .		0
295	Simulation of failure time distributions of metal lines under electromigration. Microelectronics Reliability, 2002, 42, 1469-1472.	0.9	0
296	Modeling Decoherence Effects on the Transport Properties of Mesoscopic Devices. Journal of Computational Electronics, 2003, 2, 393-396.	1.3	0
297	Challenges and solutions for numerical modeling of nanoMOSFETs. , 0, , .		0
298	Mesoscopic noise in VLSI devices. , 2003, 5115, 31.		0
299	Ballistic transport in strained-Si cavities: experiment and theory. , 0, , .		0
300	Modeling the effects of dephasing on mesoscopic noise. , 2004, , .		0
301	Modeling of Suppressed Shot Noise in Stress-Induced Leakage Currents. AIP Conference Proceedings, 2005, , .	0.3	0
302	Transition between Pauli exclusion and Coulomb interaction in the noise behavior of resonant tunneling devices. AIP Conference Proceedings, 2005, , .	0.3	0
303	Shot noise behavior of cascaded mesoscopic structures. AIP Conference Proceedings, 2005, , .	0.3	0
304	Silicon-on-insulator non-volatile memories with second-bit effect. Journal of Computational Electronics, 2006, 5, 137-142.	1.3	0
305	Editorial: Modeling and simulation of electron devices. Journal of Computational Electronics, 2006, 5, 69-70.	1.3	0
306	Modeling & Simulation - Nanotubes, Nanowires, and Nanoribbons. , 2007, , .		0

#	Article	IF	Citations
307	Session 8: Modeling and simulation - advances in modeling low dimensional structures. , 2008, , .		0
308	Time-dependent analysis of low VDD program operation in double-gate SONOS memories by full-band Monte Carlo simulation. Journal of Applied Physics, 2009, 106, 104506.	1.1	0
309	Shot noise analysis in quasi one-dimensional Field Effect Transistors. , 2009, , .		0
310	Foreword and welcome. , 2010, , .		0
311	Drain current computation in nanoscale nMOSFETs: Comparison of transport models. , 2010, , .		0
312	Experimental extraction of barrier lowering and backscattering in saturated short-channel MOSFETs. , 2010, , .		0
313	Transport and noise properties of graphene-based transistors revealed through atomistic modelling. , 2010, , .		0
314	A multi-scale approach for performance assessment of hydrogenated graphene Field-Effect Transistors. , 2010, , .		0
315	Localization and shot noise in quantum nanostructures. , 2011, , .		0
316	Sensitivity-based investigation of threshold voltage variability in 32-nm flash memory cells. , 2012, , .		0
317	Improving the efficiency of organic solar cells with graphene transparent electrode and light management: A simulation study. , 2015, , .		0
318	Toward understanding of donor-traps-related dispersion phenomena on normally-ON AlGaN/GaN HEMT through transient simulations. , 2015, , .		0
319	Attenuation limits in longitudinal phononic crystals. Journal of Applied Physics, 2017, 122, 214502.	1.1	0
320	Design of a 3T current reference for low-voltage, low-power operation. , 2018, , .		0
321	Single-poly floating-gate memory cell options for analog neural networks. Solid-State Electronics, 2021, 185, 108062.	0.8	0
322	Problems and Perspectives in Quantum-Dot Based Computation. , 2000, , 455-466.		0
323	Implementation of QCA Cells with SOI Technology. , 2006, , 143-177.		0
324	Time-Dependent Analysis of QCA Circuits with the Monte Carlo Method. , 2006, , 109-141.		0

#	Article	IF	Citations
325	Implementation of QCA Cells in GaAs Technology. , 2006, , 179-212.		0
326	Non-Invasive Charge Detectors. , 2006, , 213-227.		0
327	Devices based on 2D materials for on-chip amplification of ionization charges. , 2017, , .		0
328	Electric-field controlled spin transport in bilayer CrI₃. , 2021, , .		0
329	Stability and Startup of Non Linear LoopÂCircuits. Lecture Notes in Electrical Engineering, 2020, , 463-468.	0.3	0
330	Shot Noise in Mesoscopic Devices and Quantum Dot Networks. , 2004, , 45-52.		0
331	Electric-field controlled spin transport in bilayer CrI3. , 2021, , .		0
332	(La,Ba)SnO3 -based Thin-Film Transistors: Large-Signal Model and Scaling Projections. Physical Review Applied, 2022, 17, .	1.5	0
333	Integrating Mobile IoT Devices into the Arrowhead Framework Using Web of Things. , 2022, , .		0